

Satoshi Sugahara is an Associate Professor of Imaging Science and Engineering Laboratory, Tokyo Institute of Technology, and of Department of Electronics and Applied Physics, Tokyo Institute of Technology. His background is physical electronics, and his primary research interests include the fields of high-speed semiconductor devices and novel device concepts employing particular transport phenomena in solid state. His recent work includes the proposal and analysis of Si spin-transistors referred to as spin MOSFETs. His recent research interests have been in the heterogeneous integration technologies of high mobility materials such as Ge and III-V semiconductors and of ferromagnetic materials including half-metallic ferromagnets and ferromagnetic semiconductors on Si substrates, and in their novel CMOS device applications.

He received the Ph.D. degree in electronic engineering from Tokyo Institute of Technology. In 2000, he joined the Department of Electronic Engineering at the University of Tokyo. There, he started to study spin-electronic materials and devices. In 2005, he joined the Department of Frontier Informatics at the University of Tokyo, where he studied high performance MOSFETs with high mobility channel. Dr. Sugahara is a member of the Japan Society of Applied Physics.